We report for the first time the discovery of reversible n–p conduction type switching in a chalcogenide, NaCu$_5$S$_3$, without structural transition. AC impedance and first-principles simulations of the ionic migration confirmed the local melting trends of the hexagonal copper lattice at high temperatures, which could result in superionic conductivity within NaCu$_5$S$_3$.

There has been considerable research interest in materials with bi-stability or multi-stability, i.e. two or more stable or meta-stable electronic states under external stimuli such as temperature, pressure, light, and so on. Such bi-stable and multi-stable materials hold great potential in modern electronic applications such as sensors, transistors, resistive switches, information storage devices, etc. Recent research hotspots regarding bi-stable materials include the phase-change system, spin-crossover, metal–insulator transition, and photochromism. Representatively, Ge–Sb–Te alloys possessing controllable crystalline–amorphous phase change ability have already been widely employed in rewriteable non-volatile optical data storage systems such as compact disks (CDs), digital versatile disks (DVDs), and Blu-ray disks (BDs). Another spectacular example of bi-stability is compact disks (CDs), digital versatile disks (DVDs), and Blu-ray rewriteable non-volatile optical data storage systems such as phase change ability have already been widely employed in superionic conductivity within NaCu$_5$S$_3$.

Specific metal–organic complexes exhibit dramatic low-spin to high-spin state transitions under light irradiation or temperature variation. Recently, an emerging class of semiconductors that exhibit fascinating temperature-driven conduction type switching (i.e. n-to-p) has been discovered, which can be operated reversibly upon temperature or voltage change near room temperature. Currently known n–p switching compounds are limited to several Ag-based chalcogenides and halogen chalcogenides such as Ag$_{10}$Te$_4$Br$_3$, AgCu$_2$, AgCuSe, AgBiSe$_2$, and Ag$_2$Se, and are very rare in oxide perovskites such as Ba$_2$Sr$_{2-x}$Ti$_{2-x}$Fe$_{0.8}$Co$_{0.2}$O$_{6}$, F$_{0.64}$Nd$_{0.4}$O$_{2}$. Among them, Ag$_{10}$Te$_4$Br$_3$ was first reported to offer a combination of reversible conduction type switching and high silver mobility, which causes a thermopower drop of 1400 $\mu$V K$^{-1}$ during the transition. The p–n–p switching can be explained by temperature-induced polymorphism and the low-dimensional polytelluride sublattice with unexpected electrical states. Similar temperature-dependent p–n–p conduction type switching was observed in AgBiSe$_2$ and AgCuS, accompanied with reversible structural phase transitions and colossal changes of the thermopower values. It is believed that the presence of intermediate states of semimetals in these compounds is responsible for the occurrence of p–n–p transitions. Although several different theories have been proposed for the transformation of various temperature-dependent semiconductors caused by phase transitions, the exact mechanism is still being explored.

It should be noted that until now, almost all temperature-dependent conduction type switching is accompanied by structural phase transformations. Structural phase transition is supposed to result in not only electronic changes such as a change of band structure and spin states of the metal centers, but also unexpected changes of intrinsic conduction carrier types (electron or hole) via atomic rearrangements. In the cases of Ag$_{10}$Te$_4$Br$_3$, AgBiSe$_2$, and AgCuS, the three distinct n or p conducting states correspond to the three crystallographic polymorphs one by one, and the atomic rearrangements of the Ag–Te or Ag–Bi–Se chains are proposed to have major contributions to the conduction evolution. Therefore, firstly, it is of urgent scientific significance to explore more
temperature-dependent n–p switching materials, especially those with new mechanisms. Secondly, in the currently known p–n switching materials, the switching is highly related to the intermediate phases that only exist within a narrow temperature range (i.e., ~70 K of x-AgCuS, ~30 K of mixed x,P-Ag10Te4Br3, and ~50 K of rhombohedral AgBiSe2). Thus, it is of great practical importance to develop bi-stable n–p switching semiconductors rather than the previously reported tri-stable systems. In pursuit of novel temperature-dependent n–p switching materials, we focused on Ag- or Cu-rich chalcogenides with three-dimensional Ag/Cu sub-lattices. Such compounds always exhibit mixed ion-electron conductance at room temperature and a liquid-like behavior as temperature rises, such as AgCuS13 and AgCuSe.15 As a result, in these Ag- or Cu-rich systems, the transformation of conduction type is highly expected.

Here, we report the structural and physical property evolution of NaCuS3 as a function of temperature, which shows reversible n–p conduction type switching at elevated temperatures but without any structural phase transition. This phenomenon is confirmed by means of in situ temperature-dependent powder X-ray diffraction, comprehensive transport measurements, and thermal analysis. Based on the AC impedance results and theoretical simulations, a new mechanism of conduction type switching in Ag- or Cu-rich chalcogenides has been proposed, which we believe will provide a reference for future exploration and structural design of novel bi-stable functional materials.

A NaCuS3 sample was synthesized via a solvothermal method adopting CuS, NaOH and NH4N3S as the raw reagents. Fig. 1a shows the room temperature powder XRD pattern of the as-obtained NaCuS3, which confirms the high phase purity of the products as compared with the calculated peak positions.21 The NaCuS3 micro-crystals have a rod-like morphology and are about 30–50 μm long (Fig. S1, ESI†) and sintered samples (Fig. S2, ESI†). NaCuS3 crystallizes in the space group P6322 based on a hexagonal close-packed arrangement of S atoms (inset of Fig. 1a). In the crystal structure, there are two different copper sites: a Cu(1) atom coordinated with two S atoms with the same bond length of 2.186 Å, and a Cu(2) atom coordinated with three S atoms forming a regular triangular coordination environment with the Na–S bond length of 2.364 Å. Meanwhile, all the sodium atoms are located within the channels and coordinated with six S atoms forming regular octahedra with a Na–S bond length of 2.893(1) Å. NaCuS3 is a narrow-bandgap semiconductor with the Eg value ~0.42 eV, as reported previously.22

Fig. 1b displays the temperature dependent thermopower (S) of NaCuS3 in the temperature range of 300–725 K. The optical images of the sample used for electrical and thermal property tests are shown in Fig. S3 (ESI†). Initially, the Seebeck coefficient of NaCuS3 at room temperature is negative, indicating an n type conduction characteristic (i.e., electron is the main carrier). As temperature increases, the S value decreases gradually from ~122 μV K−1 at 325 K to ~170 μV K−1 at 500 K, and then increases sharply when the temperature increases beyond 540 K. The Seebeck coefficient changes from negative to positive at around 560 K, indicating conduction type switching from n to p type. The cooling process demonstrated that when the temperature drops, the characteristic of the material changes back to n-type (Fig. S4, ESI†). Hall coefficient measurements have been conducted to confirm the n–p switching phenomenon observed from the Seebeck coefficient. The initial negative value of the Hall coefficient also represents an n type conduction behavior of NaCuS3 at room temperature, and the positive value above 560 K represents a p type semiconducting behavior. As shown in Fig. 1c, the Hall coefficient of NaCuS3 has a dramatic negative-to-positive transition at around 560 K, indicating the change of the main carrier from electron to hole accompanying the change in the Seebeck coefficient.

The electrical conductivity evolution (Fig. S5, ESI†) and the high Hall carrier concentration of NaCuS3 as a function of temperature (Fig. S6, ESI†) represent the fact that NaCuS3 is a highly degenerate semiconductor. The conductivity value decreases monotonically when the temperature increases from room temperature to 580 K and then it remains almost constant up to 680 K, which can be attributed to the competition between increased carrier concentration and phonon scattering. We also demonstrated that the change of the electrical conductivity is also reversible and repeatable (Fig. S7, ESI†). The inset of Fig. 1c represents the power factor (PF = S2σ) of NaCuS3 as a function of temperature. As a combination of Seebeck coefficient and electrical conductivity, the PF value of NaCuS3 reaches zero at around 560 K accompanied with n–p switching. All this evidence proves the temperature dependent reversible n–p conduction type switching in NaCuS3.

In general, the phenomenon of n–p conduction type switching in semiconductors is usually accompanied with the occurrence of structural phase transitions. For example, Ag10Te4Br3 undergoes a γ → β → α phase transition during the p–n–p conduction type switching during a narrow temperature range: 310–410 K.12 AgBiSe2 and AgCuS undergo structural phase transitions from rhombohedral to cubic and orthorhombic to hexagonal to cubic symmetry, respectively.13,14,16 Fig. S8 (ESI†) shows the DSC curve of synthetive NaCuS3, which displays no obvious endothermic or exothermic peaks. The results of the TG–DTA curve of the sintered samples are consistent with this, indicating that the
increased ionic conduction in NaCu5S3 and the combined cations gradually tend to be spike-like, indicating the greatly boundarize. As temperature further increases, the two semicircles corresponding to the separate contributions from the bulk particles and grain boundaries. At temperature not only provides superionic conductivity but also the copper sublattice and is specifically related to the Cu1–Cu2 interposition migration. The copper sublattice melting at elevated temperatures not only provides superionic conductivity but also results in dramatic conduction type switching.

In summary, we synthesized a Cu-rich chalcogenide semiconductor, NaCu5S3, using a facile hydrothermal method. The material exhibits a reversible temperature-driven n-to-p conduction type transition at around 560 K but without any structural phase transition, which is distinct from all the p-n-p switching chalcogenides reported so far. By a combination of comprehensive

structure of NaCu5S3 has excellent stability (Fig. S9, ESI†). Fig. 2a shows the in situ XRD measurement results of NaCu5S3 from room temperature to 653 K. Firstly, no evident phase transition can be observed as almost all of the XRD peaks remain the same but only move to lower 2θ angles, corresponding to normal lattice expansion as temperature increases. This is distinct from other known chalcogenides with temperature-dependent conduction type conversion. The underlying mechanism of the temperature-dependent n–p conduction type switching in NaCu5S3 is different from other chalcogenides. Secondly, the evolution of the powder XRD patterns during heating and cooling processes is reversible, as they return to the initial profile with almost the same cell parameters after cooling down to room temperature.

Fig. 2b shows the temperature dependence of lattice parameters derived from LeBail fitting of the powder XRD patterns. Below 523 K, the lattice parameters of both a and c increase linearly with increasing temperature. This is the distinct lattice expansion along the c-axis deviates from the linear law above 523 K, corresponding to the occurrence of the n–p transition. This points to a subtle local structure change accompanying the conduction type switching. A reasonable speculation referring to the previous cases of superionic solid electrolytes is that the copper sublattice begins to melt locally, while the rigid sublattice of the S atom remains unchanged.

The ionic conductivity of NaCu5S3 was measured using the 6w->AC impedance method. Fig. 3a shows the representative Nyquist plots for NaCu5S3 from room temperature to 653 K. At temperatures lower than 533 K, most of the impedance plots are composed of two partially overlapped semicircles corresponding to the separate contributions from the bulk particles and grain boundaries. As temperature further increases, the two semicircles gradually tend to be spike-like, indicating the greatly increased ionic conduction in NaCu5S3 and the combined component of inductance. The total ionic conductivities were calculated based on the intercept to the real axis, and the result is shown in Fig. 3b. Notably, the ionic conductivity rises rapidly in the temperature range of 500–600 K, from \(3.5 \times 10^{-3} \text{ S cm}^{-1}\) to \(15.0 \times 10^{-3} \text{ S cm}^{-1}\). This can be attributed to the local melting of the copper sublattice by comparing to the similar behavior of PbF2, CaF2 and Cu2–Se. High copper ionic mobility or even a liquid-like copper sublattice has been observed in a collection of copper thermoelcectrics. Considering the absence of structural phase transition, one has reasons to believe that the melting of the copper sublattice is closely related to the n-p type conduction switching in NaCu5S3. It is also notable that the overall ionic conductivity of NaCu5S3 reflected from the AC impedance spectra is very complex, and at least consists of the contributions from Na⁺ ions, Cu⁺ ions and electronic conductivity involving both electrons and holes.

To gain more insights into the superionic conductivity and copper sublattice melting in NaCu5S3, we performed a DFT simulation to evaluate the migration of monovalent cations Na⁺ and Cu⁺ within the NaCu5S3 structure. Fig. 4a shows the sublattice of Na⁺ and Cu⁺ cations, in which two distinct Cu atoms can be observed and all the Na atoms locate in the same chemical environment forming a one-dimensional chain along the c-axis. Firstly, we can check the atomic distances of Cu1–Cu1, Cu2–Cu2 and Na1–Na1 of 3.78 Å, 3.26 Å and 3.60 Å, respectively. The closest atomic distance is between Cu1 and Cu2, and is only 2.71 Å. Such a small distance is beneficial to reduce the migration barrier between Cu1 and Cu2, thereby facilitating the migration between Cu1 and Cu2. Fig. 4b provides the calculated cation migration barrier from one cation site to the nearest one: ~1.8 eV for Cu1–Cu1, ~1.7 eV for Cu2–Cu2, ~0.9 eV for Na1–Na1 and ~0.4 eV for Cu1–Cu2, respectively. This result indicates that compared to the other three possibilities, the migration within Cu1–Cu2 sites requires the least active energy. Thus, local melting will very likely occur within the copper sublattice and is specifically related to the Cu1–Cu2 interposition migration. The copper sublattice melting at elevated temperatures not only provides superionic conductivity but also results in dramatic conduction type switching.

In summary, we synthesized a Cu-rich chalcogenide semiconductor, NaCu5S3, using a facile hydrothermal method. The material exhibits a reversible temperature-driven n-to-p conduction type transition at around 560 K but without any structural phase transition, which is distinct from all the p-n-p switching chalcogenides reported so far. By a combination of comprehensive
experimental characterization methods of in situ temperature-dependent powder XRD, Seebeck and Hall coefficient analysis, AC impedance analysis and DFT calculations, we demonstrate that the temperature-dependent n–p switching in NaCu$_5$S$_3$ is driven by copper sublattice melting. The discovery of this new mechanism bridges functional semiconducting materials and superionic solid electrolytes. Compared with common p- or n-type semiconductors and p–n junctions made from them, temperature-dependent p–n switching materials show potential in the concept of “dual-control” either by external environments or by artificial operations. We believe that future exploration of ionic conducting materials with order–disorder transitions or sublattice melting behaviors will provide more temperature-dependent conduction type switching materials.

Conflicts of interest

There are no conflicts to declare.

Notes and references